Supplementary materials for

Multi-shaped strain soliton networks and moiré-potential-modulated band edge states in twisted bilayer SiC

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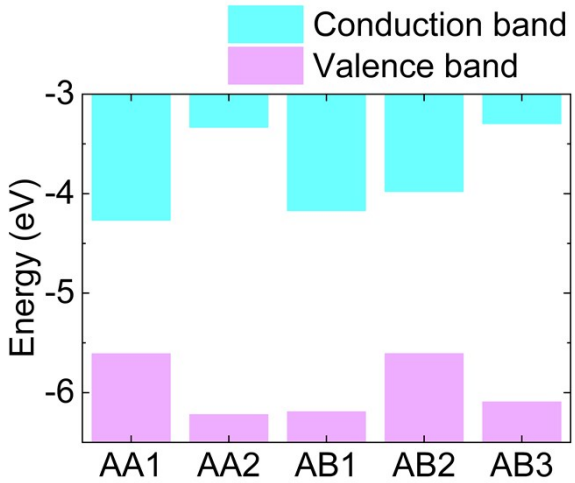

Fig.1. The band edge of bilayer SiC calculated by HSE functionals at high-symmetry stackings with rigid shift interlayer distance of 3.3 Å.

The stacking energies of bilayer SiC at high symmetry stackings are calculated as

$E_{stack} = 2E_{monolayer} - E_{bilayer}$.

Table 1. The interlayer distance of bilayer SiC at high-symmetry stackings (HSS)

HSS	AA1	AA2	AB1	AB2	AB3
Interlayer distance (Å)	3.77	2.21	3.24	3.65	3.15
Total energy (eV)	1.33	0	0.90	1.31	0.67

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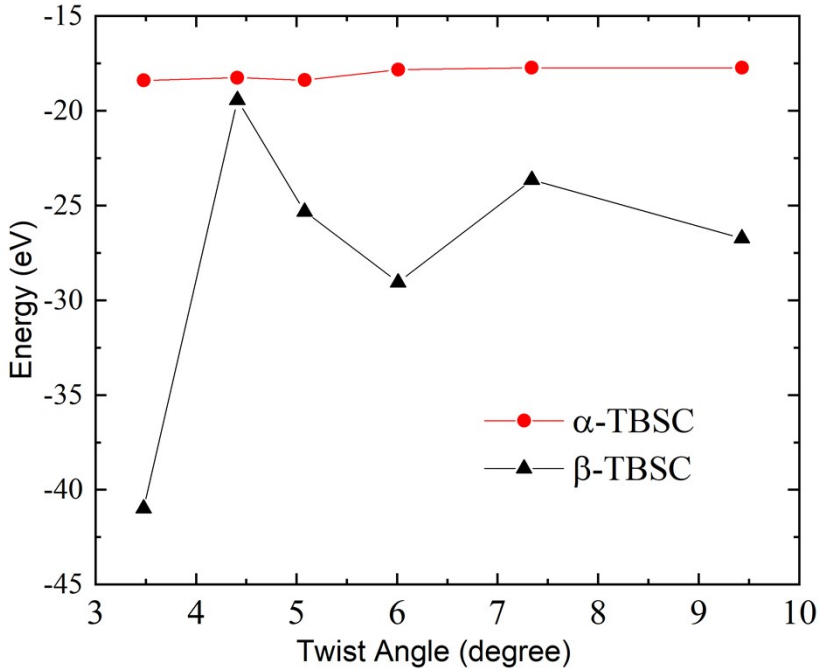

Fig. 2. The cohesive energy of TBSC as a function of twist angle.

Table 1. The (m,n) and number of atoms in TBSC studied in this work

Twist Angle	(m,n)	Number of atoms
3.48	(9,10)	1084
4.41	(7,8)	676
5.08	(6,7)	508
6.01	(5,6)	364
7.34	(4,5)	244
9.43	(3,4)	148